

**AMENDMENTS TO THE SPECIFICATION:**

Please replace paragraphs [0001], [0015], and [0048] of the Specification with the following paragraphs:

[0001] Plasma processing apparatuses are used, e.g., for plasma etching of semiconducting, dielectric and metallic materials, ~~physical-vapor-deposition~~, plasma enhanced chemical vapor deposition ("PECVD"), ~~physical-vapor-deposition ("PVD")~~, ~~ion-implantation~~, and resist removal.

[0015] In order to enhance the uniformity of plasma processing of a substrate in a plasma processing apparatus, it is desirable to control the temperature at exposed surfaces of the substrate at which etching occurs, on which material is deposited (e.g., by a PECVD or ~~PVD~~ technique), and/or at which photoresist is removed.

[0048] The substrate support 40 can be used in a plasma processing apparatus in which various plasma processing operations including plasma etching, ~~physical-vapor-deposition~~, plasma enhanced chemical vapor deposition (PECVD), ~~ion-implantation~~, and/or resist removal are performed.